EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S91	10288	257/25,81,91,95,98-100,103. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 17:03
S90	2936	216/24,41.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 17:03
S89	4027	438/22,46,47,918,9.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 17:03
S88	3	"20020132083"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 13:45
S87	45	imprint$3 same teos	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 13:41
S86	64	imprint same ((silicon-containing) or teos)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 13:36
S85	27	(teos with pmma)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 13:32
S81	2316	mask with (teos or hmda)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 13:28

S80	2316	mask with teos	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 12:12
S79	93	(micro$1contact print$3 or nano$1imprint$3 or mold or emboss$3) and (silicon-containing) and teos	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:48
S78	3072	(micro$1contact print$3 or nano$1imprint$3 or mold or emboss$3) and (silicon-containing)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:48
S77	3974	(micro$1contact print$3 or nano$1imprint$3 or mold or emboss$3) and (silicon-containing or hmds)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:47
S76	0	(micro$1contact print$3 or nano$1imprint$3 or emboss $3) and S75	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:46
S75	242	(TEOS or TMOS) with hmds	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:44
S74	230	TEOS with hmds	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:43
S73	3	(micro$1contact print$3 or nano$1imprint$3 or mold or emboss$3) and S66	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:36
S72	0	S66 and S70	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:36

S71	353	S70 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:27
S70	575	(micro$1contact print$3 or nano$1imprint$3 or mold or emboss$3) same (TEOS or TMOS)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:27
S69	22	mask same mold same TEOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:24
S68	1	resist same mold same TEOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:24
S67	0	resist with mold with TEOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:23
S66	402	S65 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:22
S65	591	S63 same etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:21
S64	487	S63 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:20
S63	785	resist with TEOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:20

S62	84	S49 and S59 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:18
S61	11	S60 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:16
S60	78	(photonic crystal) and S59	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:16
S59	2091	(micro$1contact print$3 or nano-imprint$3 or mold) same resist same etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:16
S58	15188	(micro$1contact print$3 or nano-imprint$3 or mold) same resist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:15
S57	70	S56 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:10
S56	192	(photonic crystal) same resist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:10
S55	10	(photonic crystal) same (mold) same resist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 11:09
S54	12	S52 and resist	USPAT	ADJ	ON	2008/12/02 10:55

S53	0	S52 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:54
S52	20	("2005/0082545").URPN.	USPAT	ADJ	ON	2008/12/02 10:49
S51	2	S50 and "20050082545"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:43
S50	89	S47 and S49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:33
S49	304219	(light-emitting OR light emitting OR electroluminescen$2 OR electro-luminescen$2) ADJ (diode OR device OR apparatus OR structure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:33
S48	2106	S47 and (master or mold)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:32
S47	2231	S46 and (@ad<"20031112" OR @pd<"20031111")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:31
S46	3466	S44 same resist same etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:30
S45	21611	S44 same resist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:29

S44	1545211	master or mold or imprint	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:29
S43	33	US-20040253817-$.DID. OR US-4394196-$.DID. OR US-5981354-$.DID. OR US-6080659-$.DID. OR US-6103574-$.DID. OR US-6136662-$.DID. OR US-6143625-$.DID. OR US-6288454-$.DID. OR US-6375870-$.DID. OR US-6610463-$.DID. OR US-4301322-$.DID. OR US-6878634-$.DID. OR US-4381700-$.DID. OR US-6924023-$.DID. OR US-6943117-$.DID. OR US-6949199-$.DID. OR US-6964793-$.DID.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:16
S42	35	S41 and (resist) and mold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:09
S41	225	((Imada near2 Aya) or (tohru near2 den)).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 10:08
S40	1	("2004/0253817").URPN.	USPAT	ADJ	ON	2008/12/02 10:05
S39	1	"10575489"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/12/02 09:38

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